



General Description:

- (1) Chip Dimension
 Chip Size= 7 mil x 9 mil (180um x 230um)
 Chip Thickness= 100±10 μm
 P/N Bonding Pad = 70±5 μm
- (2) Electrode:
 P (Anode) → Au
 N (Cathode) → Au
- (3) Structure:
 Refer to drawing
 SiO₂ Passivated surface

Electro-optical Characteristics(Ta=RT)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V _F	2.7	-	3.0	V	I _F = 5mA
Dominant Wavelength	λ _D	450	-	470	nm	I _F = 5mA
Reverse Current	I _R	0	-	2	μA	V _R =-5V

亮度 Luminous Intensity(I _v) mcd at I _F =5mA	波長 Dominant Wavelength(nm)								
	Range	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465	465~467.5	467.5~470
5~10									
10~15									
15~20									
20~25									
25~30									
30~35									
35~40									

Features:

- 1. High Luminous Intensity
- 2. Long Operation Life
- 3. High Current; Pulse Operation
- 4. Indoor/Outdoor Applications

Notes:

- 1. Dominant wavelength includes an error of ± 1nm
- 2. Luminous intensity includes an error of ±10%
- 3. Luminous intensity is measured on bare chip
- 4. InGaN LED is sensitive to ESD